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**George G. Barclay**, Rohm and Haas Electronic Materials (United States)  
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- 5 Molecular Resists  
**Clifford L. Henderson**, Georgia Institute of Technology (United States)  
**Mark H. Somervell**, Tokyo Electron America, Inc. (United States)
- 6 Novel Materials, Processes, and Applications I  
**Adam R. Pawloski**, Affymetrix, Inc. (United States)  
**Vivek M. Prabhu**, National Institute of Standards and Technology (United States)
- 7 ARCs and Multilayer Processes  
**Ralph R. Dammel**, AZ Electronic Materials (United States)  
**Douglas J. Guerrero**, Brewer Science, Inc. (United States)
- 8 EUV Resist Materials and Processes  
**E. Steve Putna**, Intel Corporation (United States)  
**Nobuyuki N. Matsuzawa**, Sony Atsugi Technology Center (Japan)
- 9 Resist Fundamentals  
**Gregory M. Wallraff**, IBM Almaden Research Center (United States)  
**Ralph R. Dammel**, AZ Electronic Materials (United States)
- 10 Simulation of Resist Processes  
**Adam R. Pawloski**, Affymetrix, Inc. (United States)  
**Vivek M. Prabhu**, National Institute of Standards and Technology (United States)
- 11 LER/LWR Behavior in Resists  
**Qinghuang Lin**, IBM Thomas J. Watson Research Center (United States)  
**Mark H. Somervell**, Tokyo Electron America, Inc. (United States)
- 12 Novel Materials, Processes, and Applications II  
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